HM62W8128 Series

131,072-word × 8-bit High Speed CMOS Static RAM

HITACHI

Description

The Hitachi HM62W8128 is a CMOS static RAM organized 131,072-word × 8-bit. It realizes higher density, higher performance and low power consumption by employing 0.8 µm Hi-CMOS process technology. It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. The device, packaged in a 525-mil SOP (460-mil body SOP) or a 8 × 20 mm TSOP with thickness of 1.2 mm, is available for high density mounting. TSOP package is suitable for cards, and reverse type TSOP is also provided.

Features

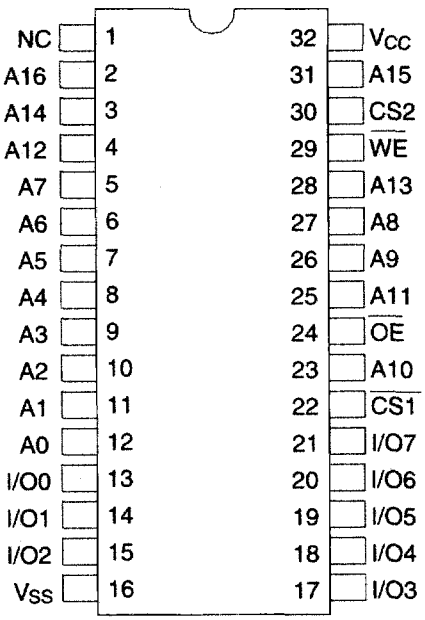
- High speed
  - — Fast access time: 100/120 ns (max)
- Low power
  - — Active: 23 mW (typ)
  - — Standby: 4 µW (typ)
- Single 3.3 V supply
- Completely static memory
  No clock or timing strobe required
- Equal access and cycle times
- Common data input and output
  Three state output
- All inputs and outputs CMOS compatible.
- Capability of battery backup operation
  2 chip selection for battery backup

Ordering Information

Type No.	Access Time	Package
HM62W8128LFP-10	100 ns	525-mil 32-pin plastic SOP (FP-32D)
HM62W8128LFP-12	120 ns	
HM62W8128LFP-10SL	100 ns	
HM62W8128LFP-12SL	120 ns	
HM62W8128LT-10	100 ns	8mm × 20mm 32-pin TSOP (normal type) (TFP-32D)
HM62W8128LT-12	120 ns	
HM62W8128LT-10SL	100 ns	
HM62W8128LT-12SL	120 ns	
HM62W8128LR-10	100 ns	8mm × 20mm 32-pin TSOP (reverse type) (TFP-32DR)
HM62W8128LR-12	120 ns	
HM62W8128LR-10SL	100 ns	
HM62W8128LR-12SL	120 ns	

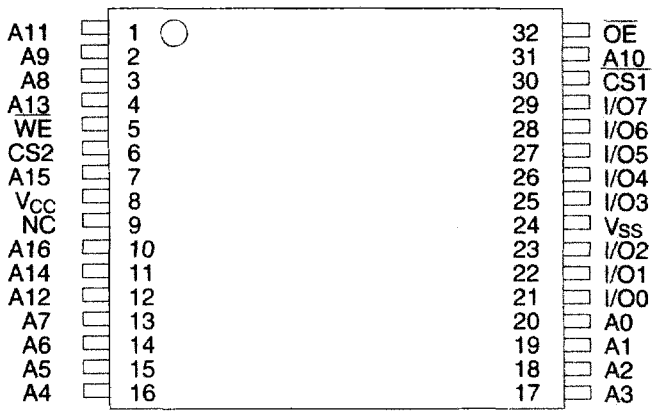
Pin Arrangement

HM62W8128LFP Series



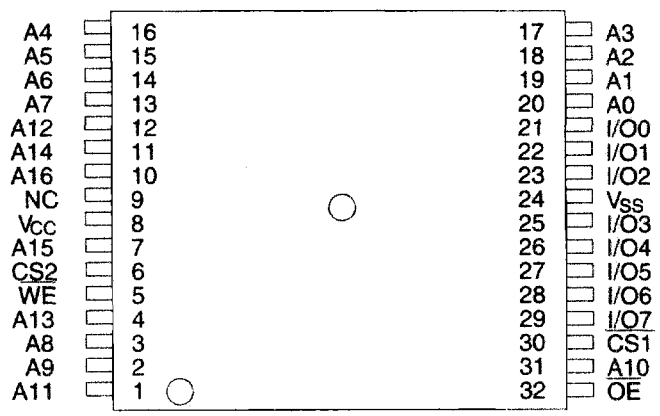
(Top View)

HM62W8128LT Series



(Top View)

HM62W8128LR Series

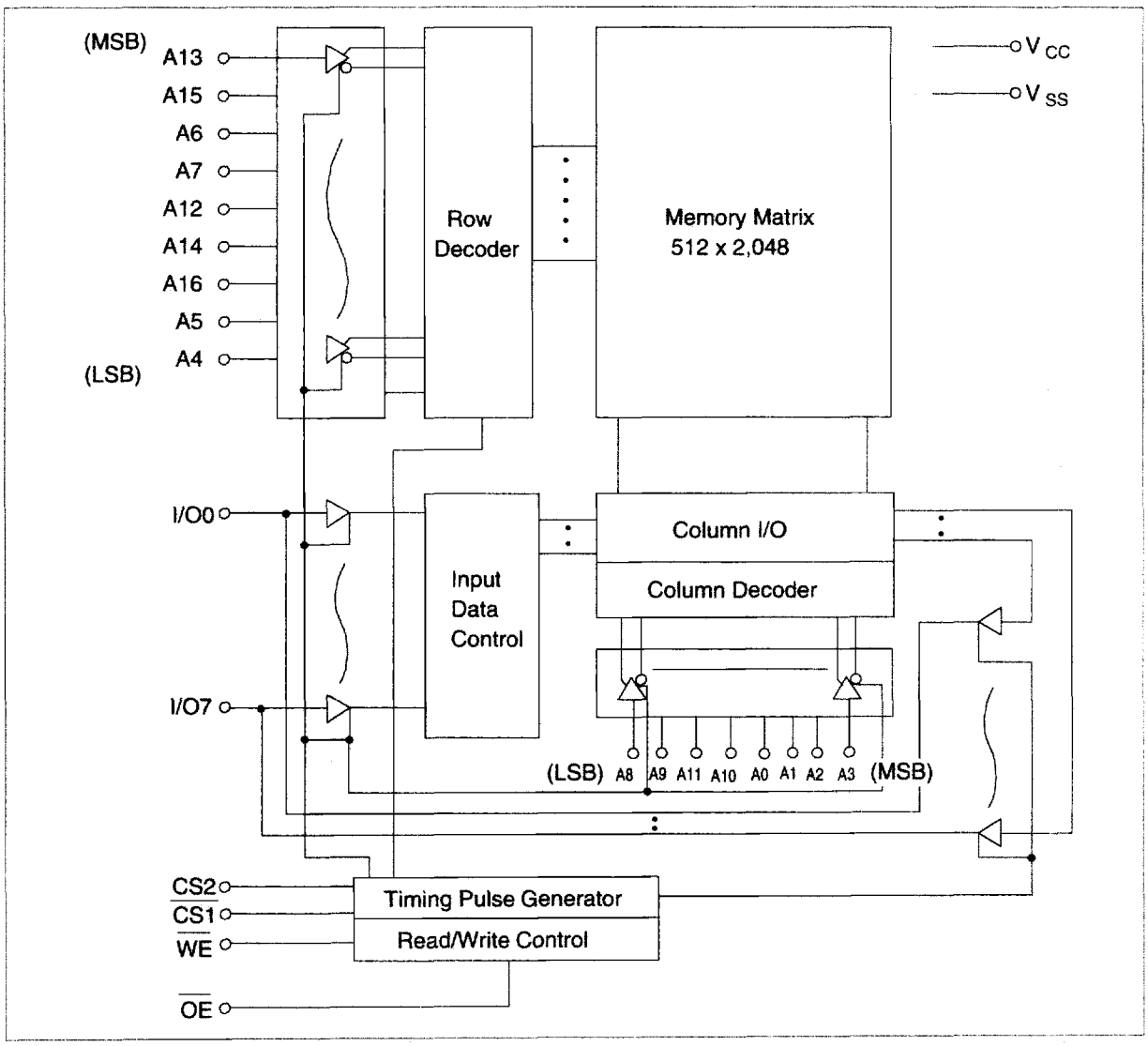


(Top View)

Pin Description

Pin Name	Function
A0 – A16	Address
I/O0 – I/O7	Input/output
$\overline{CS1}$	Chip select 1
CS2	Chip select 2
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
NC	No connection
V_{CC}	Power supply
V_{SS}	Ground

Block Diagram



Function Table

$\overline{CS1}$	CS2	$\overline{OE}$	$\overline{WE}$	Mode	V_{CC} Current	I/O Pin	Ref. Cycle
H	X	X	X	Standby	I_{SB}, I_{SB1}	High-Z	—
X	L	X	X	Standby	I_{SB}, I_{SB1}	High-Z	—
L	H	H	H	Output disable	I_{CC}	High-Z	—
L	H	L	H	Read	I_{CC}	Dout	Read cycle
L	H	H	L	Write	I_{CC}	Din	Write cycle (1)
L	H	L	L	Write	I_{CC}	Din	Write cycle (2)

Note: X: H or L

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V_{SS}	V_{CC}	−0.5 to +5.5	V
Voltage on any pin relative to V_{SS} *1	V_T	−0.5*2 to V_{CC} + 0.3*3	V
Power dissipation	P_T	1.0	W
Operating temperature	Topr	0 to +70	°C
Storage temperature	Tstg	−55 to +125	°C
Storage temperature under bias	Tbias	−10 to +85	°C

Notes: 1. With respect to V_{SS}
2. −1.2 V for pulse half-width ≤ 30 ns
3. Maximum voltage is 5.5 V

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	3.0	3.3	3.6	V
	V_{SS}	0	0	0	V
Input voltage	V_{IH}	2.2	—	V_{CC} + 0.3	V
	V_{IL}	−0.3 *1	—	0.4	V

Note: 1. −1.2 V for pulse half-width ≤ 30 ns

DC Characteristics (Ta = 0 to +70°C, V_{CC} = 3.3 V ±0.3 V, V_{SS} = 0 V)

Parameter	Symbol	Min	Typ*1	Max	Unit	Test Conditions
Input leakage current	$\|I_{LI}\|$	—	—	1	µA	Vin = V_{SS} to V_{CC}
Output leakage current	$\|I_{LO}\|$	—	—	1	µA	$\overline{CS1}$ = V_{IH} or CS2 = V_{IL} or $\overline{OE}$ = V_{IH} or $\overline{WE}$ = V_{IL}, $V_{I/O}$ = V_{SS} to V_{CC}
Operating power supply current: DC	I_{CC}	—	6	10	mA	$\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/V_{IL}, $I_{I/O}$ = 0 mA
Operating power supply current	I_{CC1}	—	20	25	mA	Min cycle, duty = 100%, $\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/V_{IL}, $I_{I/O}$ = 0 mA
	I_{CC2}	—	7	10	mA	Cycle time = 1 µs, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS1}$ ≤ 0.2 V, CS2 ≥ V_{CC} − 0.2 V, V_{IH} ≥ V_{CC} − 0.2 V, V_{IL} ≤ 0.2 V
Standby power supply current: DC	I_{SB}	—	0.5	2	mA	(1) $\overline{CS1}$ = V_{IH}, CS2 = V_{IH} or (2) CS2 = V_{IL}
Standby power supply current (1): DC	I_{SB1} (L version)	—	1.2	70	µA	0 V ≤ Vin ≤ V_{CC} (1) $\overline{CS1}$ ≥ V_{CC} − 0.2 V, CS2 ≥ V_{CC} − 0.2 V or (2) 0 V ≤ CS2 ≤ 0.2 V
	I_{SB1} (L-SL version)	—	1.2	30	µA	
Output voltage	V_{OL}	—	—	0.1	V	I_{OL} = 100 µA
	V_{OH}	2.9	—	—	V	I_{OH} = −100 µA

Note: 1. Typical values are at V_{CC} = 3.3 V, Ta = +25°C and not guaranteed.

Capacitance (Ta = 25°C, f = 1.0 MHz)*1

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Input capacitance	Cin	—	—	8	pF	Vin = 0 V
Input/output capacitance	$C_{I/O}$	—	—	10	pF	$V_{I/O}$ = 0 V

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = 0 to +70°C, V_{CC} = 3.3 V ± 0.3 V, unless otherwise noted.)

Test Conditions

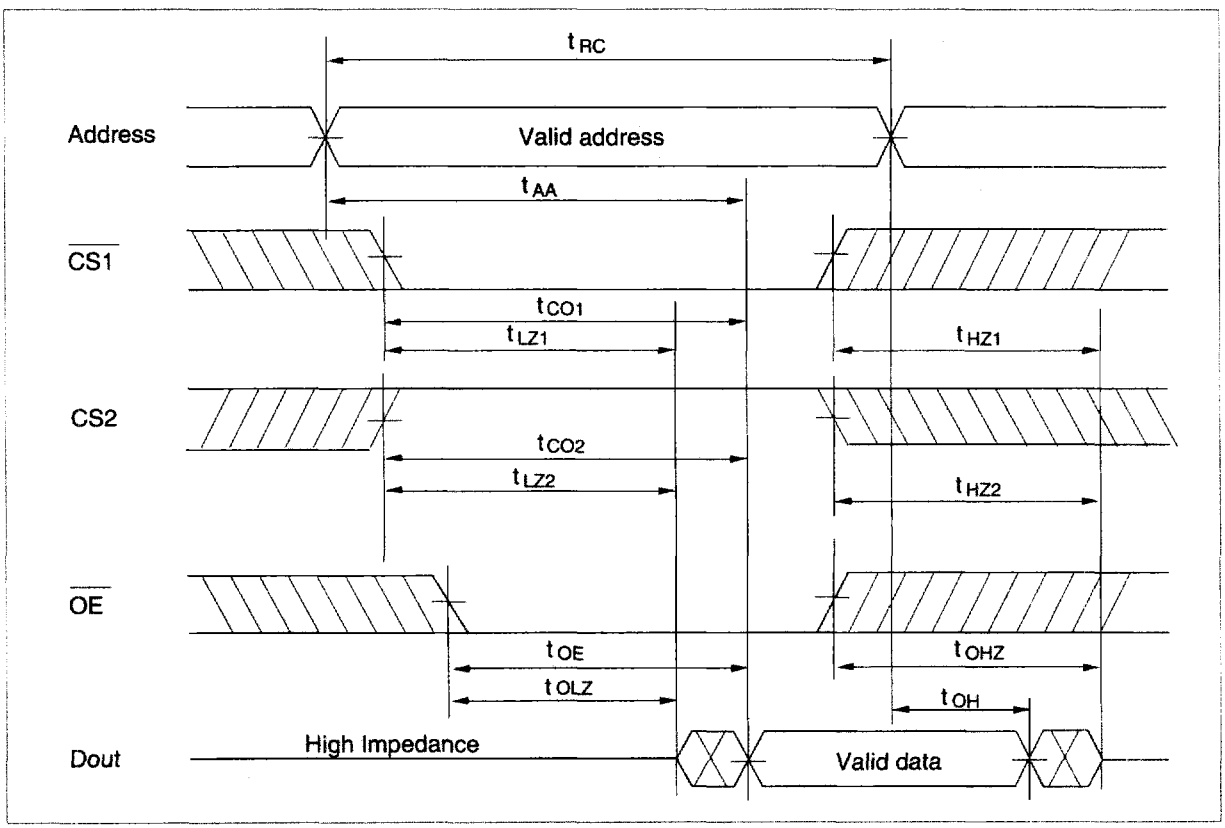
- Input pulse levels: 0.4 V to 2.4 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.5 V
- Output load: 1 TTL Gate and CL (50 pF) (Including scope & jig)

Read Cycle

		HM62W8128-10		HM62W8128-12			
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Unit**	**Notes**
Read cycle time	t_{RC}	100	—	120	—	ns	
Address access time	t_{AA}	—	100	—	120	ns	
Chip selection to output valid	t_{CO1}	—	100	—	120	ns	
	t_{CO2}	—	100	—	120	ns	
Output enable to output valid	t_{OE}	—	80	—	100	ns	
Chip selection to output in low-Z	t_{LZ1}	15	—	15	—	ns	2, 3
	t_{LZ2}	15	—	15	—	ns	2, 3
Output enable to output in low-Z	t_{OLZ}	10	—	10	—	ns	2, 3
Chip deselection to output in high-Z	t_{HZ1}	0	40	0	50	ns	1, 2, 3
	t_{HZ2}	0	40	0	50	ns	1, 2, 3
Output disable to output in high-Z	t_{OHZ}	0	40	0	50	ns	1, 2, 3
Output hold from address change	t_{OH}	15	—	15	—	ns	

Notes: 1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
2. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
3. This parameter is sampled and not 100% tested.

Read Timing Waveform ($\overline{WE}$ = V_{IH})



Write Cycle

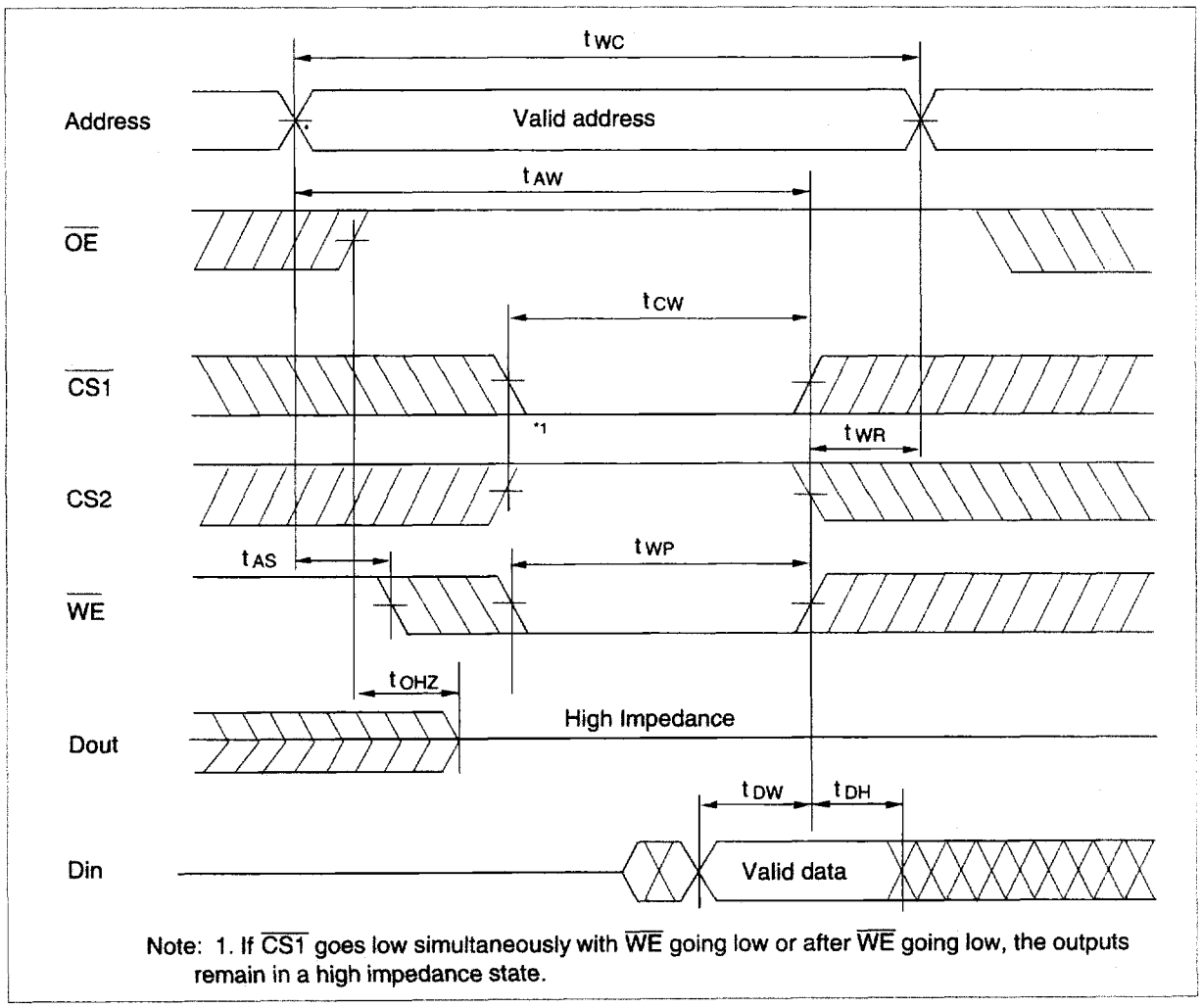
Parameter	Symbol	HM62W8128-10 Min	HM62W8128-10 Max	HM62W8128-12 Min	HM62W8128-12 Max	Unit	Notes
Write cycle time	t_{WC}	100	—	120	—	ns	
Chip selection to end of write	t_{CW}	90	—	110	—	ns	
Address setup time	t_{AS}	0	—	0	—	ns	
Address valid to end of write	t_{AW}	90	—	110	—	ns	
Write pulse width	t_{WP}	80	—	100	—	ns	
Write recovery time	t_{WR}	0	—	0	—	ns	
Write to output in high-Z	t_{WHZ}	0	40	0	50	ns	10
Data to write time overlap	t_{DW}	50	—	60	—	ns	
Write hold from write time	t_{DH}	0	—	0	—	ns	
Output active from end of write	t_{OW}	10	—	10	—	ns	10
Output disable to output in High-Z	t_{OHZ}	0	40	0	50	ns	

Notes: 1. A write occures during the overlap of a low $\overline{CS1}$, a high CS2, and a low $\overline{WE}$. A write begins at the latest transition among $\overline{CS1}$ going low, CS2 going high, and $\overline{WE}$ going low. A write ends at the earliest transition among $\overline{CS1}$ going high, CS2 going low, and $\overline{WE}$ going high. t_{WP} is measured from the beginning of write to the end of write.

2. t_{CW} is measured from the later of $\overline{CS1}$ going low or CS2 going high to the end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the earliest of $\overline{CS1}$ or $\overline{WE}$ going high or CS2 going low to the end of write cycle.
5. During this period, I/O pins are in the output state; therefore, the input signals of the opposite phase to the outputs must not be applied.
6. This parameter is sampled and not 100% tested.
7. In the cycle with $\overline{OE}$ low fixed, t_{WP} must satisfy the following equation to avoid a problem of data bus contention.

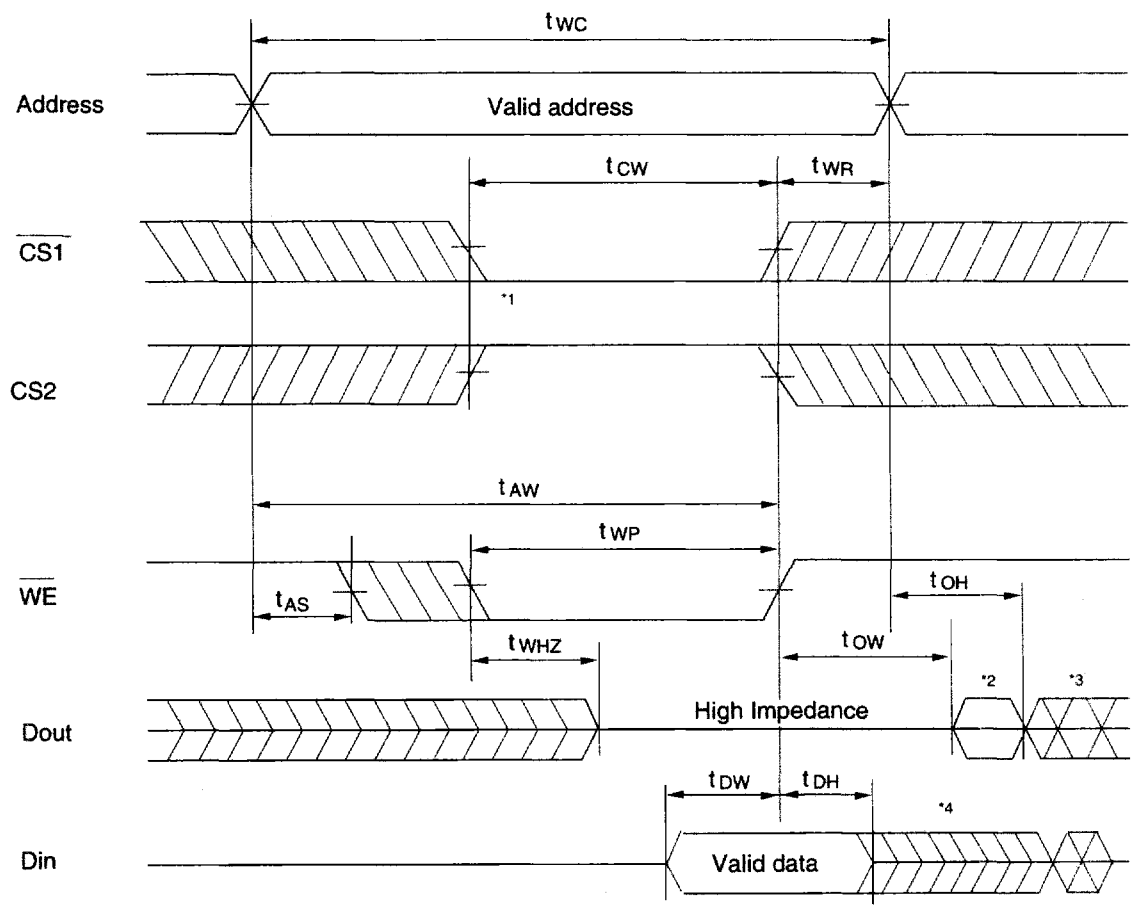
   $t_{WP} \geq t_{DW}$ min + t_{WHZ} max

Write Timing Waveform (1) ($\overline{OE}$ Clock)



Note: 1. If $\overline{CS1}$ goes low simultaneously with $\overline{WE}$ going low or after $\overline{WE}$ going low, the outputs remain in a high impedance state.

Write Timing Waveform (2) ($\overline{OE}$ Low Fixed)



Notes: 1. If $\overline{CS1}$ goes low simultaneously with $\overline{WE}$ going low or after $\overline{WE}$ going low, the outputs remain in a high impedance state.

2. Dout is the same phase of the latest written data in this write cycle.

3. Dout is the read data of next address.

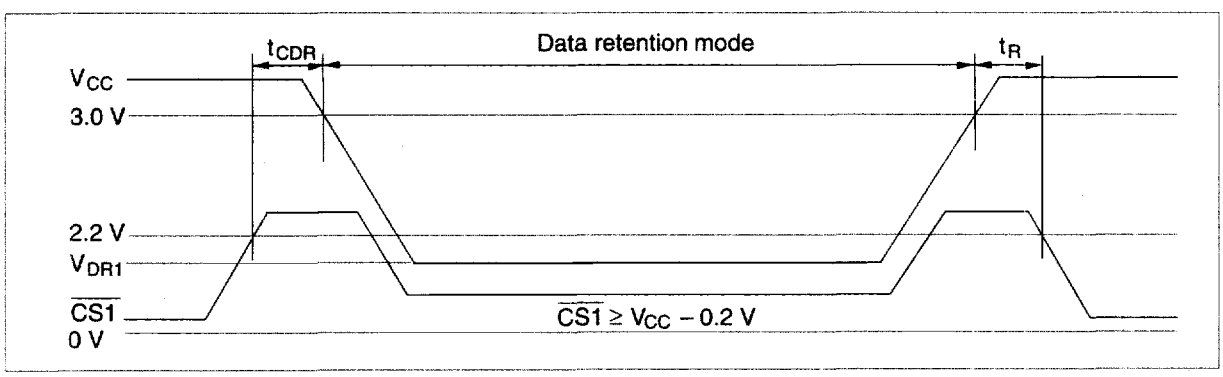
4. If $\overline{CS1}$ is low and CS2 high during this period, I/O pins are in the output state. Therefore, the input signals of the opposite phase to the outputs must not be applied to them.

Low V_{CC} Data Retention Characteristics (Ta = 0 to +70°C)

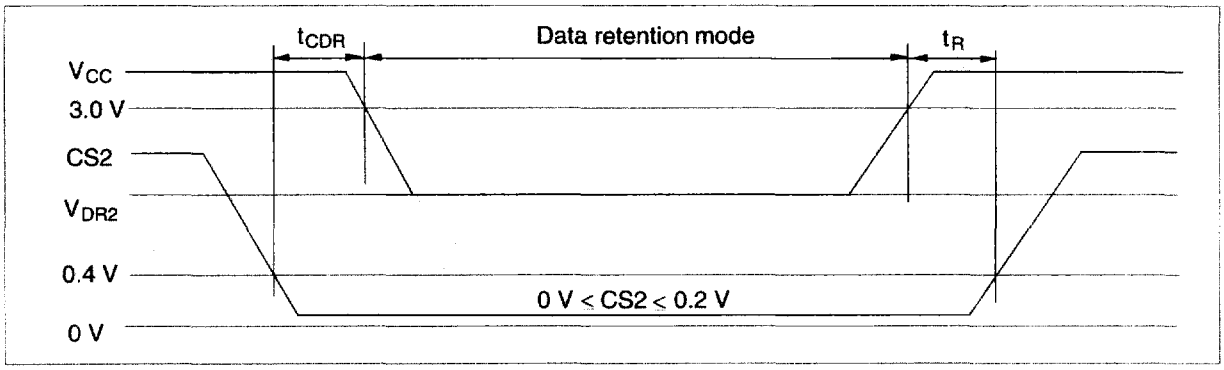
Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions[*3]
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$\overline{CS1} \geq V_{CC}$ –0.2 V, $CS2 \geq V_{CC}$ –0.2 V or 0 V ≤ CS2 ≤ 0.2 V Vin ≥ 0 V
Data retention current	I_{CCDR} (L-version)	—	1	50[*1]	µA	V_{CC} = 3.0 V, Vin ≥ 0V $\overline{CS1} \geq V_{CC}$ – 0.2 V, $CS2 \geq V_{CC}$ – 0.2 V or 0 V ≤ CS2 ≤ 0.2 V
	I_{CCDR} (L-SL version)	—	1	15[*2]	µA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t_R	5	—	—	ms	

Notes: 1. 20 µA max at Ta = 0 to 40°C (L-version).
2. 3 µA max at Ta = 0 to 40°C (L-SL version).
3. CS2 controls address buffer, $\overline{WE}$ buffer, $\overline{CS1}$ buffer, $\overline{OE}$ buffer, and Din buffer. If CS2 controls data retention mode, Vin levels (address, $\overline{WE}$, $\overline{OE}$, $\overline{CS1}$, I/O) can be in the high impedance state. If $\overline{CS1}$ controls data retention mode, CS2 must be $CS2 \geq V_{CC}$ – 0.2 V or 0 V ≤ CS2 ≤ 0.2 V. The other input levels (address, $\overline{WE}$, OE, I/O) can be in the high impedance state.

Low V_{CC} Data Retention Timing Waveform (1) ($\overline{CS1}$ Controlled)

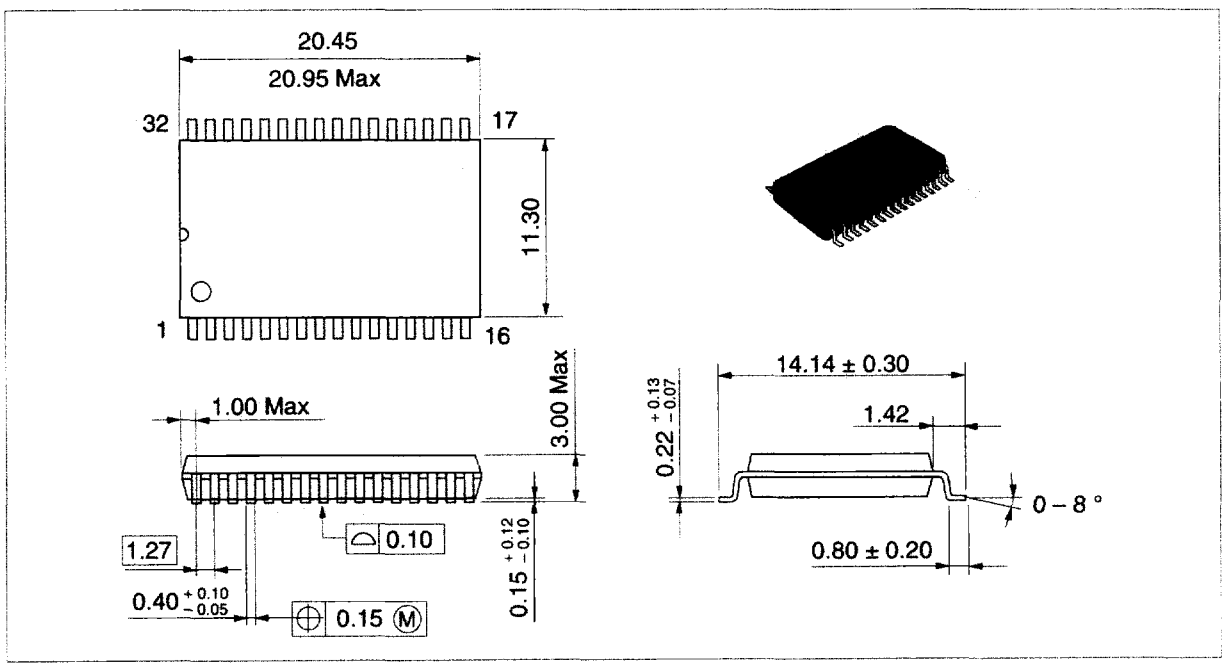


Low V_{CC} Data Retention Timing Waveform (2) (CS2 Controlled)



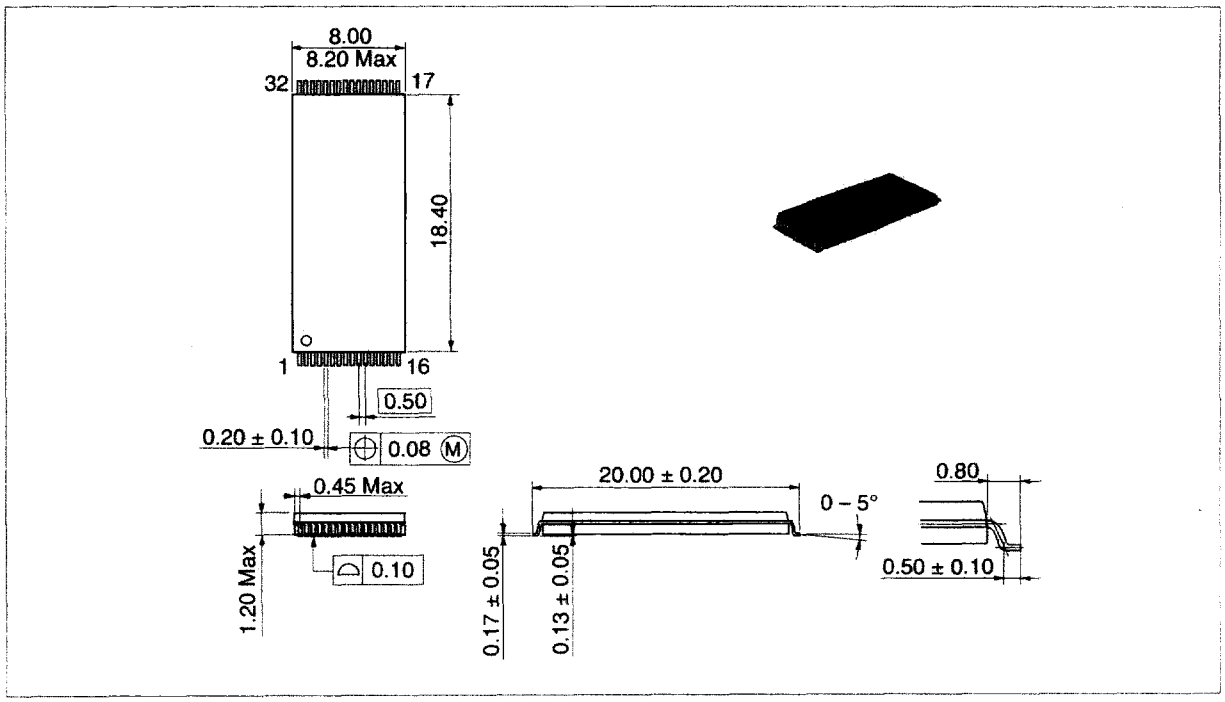
Package Dimensions

HM62W8128LFP Series (FP-32D) Unit: mm



HM62W8128LT Series (TFP-32D)

Unit: mm



HM62W8128LR Series (TFP-32DR) Unit: mm